

# isc N-Channel MOSFET Transistor IRFR13N15D, IIRFR13N15D

### FEATURES

- Static drain-source on-resistance: R<sub>D</sub>s(on)≤180mΩ
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

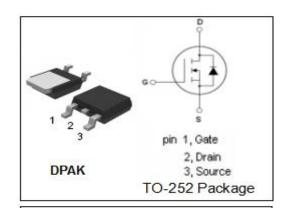
· High frequency DC-DC converters

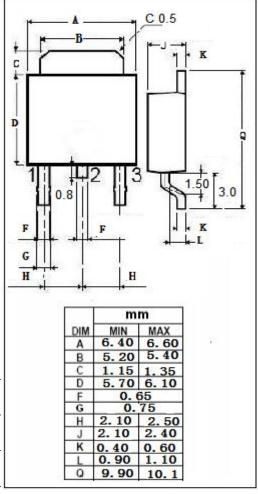
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                                  | VALUE   | UNIT         |  |
|------------------|--|---------|--------------|--|
| V <sub>DSS</sub> | Drain-Source Voltage                       | 150     | V            |  |
| V <sub>GS</sub>  | Gate-Source Voltage                        | ±30     | V            |  |
| I <sub>D</sub>   | Drain Current-Continuous                   | 14      | Α            |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed                | 56      | А            |  |
| P <sub>D</sub>   | Total Dissipation @T <sub>C</sub> =25°C 86 |         | W            |  |
| Tj               | Max. Operating Junction Temperature 175    |         | $^{\circ}$ C |  |
| T <sub>stg</sub> | Storage Temperature                        | -55~175 | $^{\circ}$   |  |

## • THERMAL CHARACTERISTICS

| SYMBOL   | PARAMETER                             | MAX  | UNIT |
|----------|---------------------------------------|------|------|
| Rth(j-c) | Channel-to-case thermal resistance    | 1.75 | °C/W |
| Rth(j-a) | Channel-to-ambient thermal resistance | 110  | °C/W |







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## **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | ТҮР | MAX  | UNIT |  |  |  |
|---------------------|--------------------------------|--|-----|-----|------|------|--|--|--|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A               | 150 |     |      | V    |  |  |  |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =250 μ A | 3   |     | 5.5  | V    |  |  |  |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =8.3A                 |     |     | 180  | mΩ   |  |  |  |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±30V                                     |     |     | ±0.1 | μА   |  |  |  |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =150V; V <sub>GS</sub> = 0V                |     |     | 25   | μА   |  |  |  |
| $V_{SD}$            | Diode forward voltage          | I <sub>s</sub> =8.3A, V <sub>GS</sub> = 0V                 |     |     | 1.3  | V    |  |  |  |

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